

## 300-mW STEREO AUDIO POWER AMPLIFIER

• 300-mW Stereo Output

FXAS

STRUMENTS

- PC Power Supply Compatibility 5-V and 3.3-V Specified Operation
- Shutdown Control
- Internal Midrail Generation
- Thermal and Short-Circuit Protection
- Surface-Mount Packaging
- Functional Equivalent of the LM4880

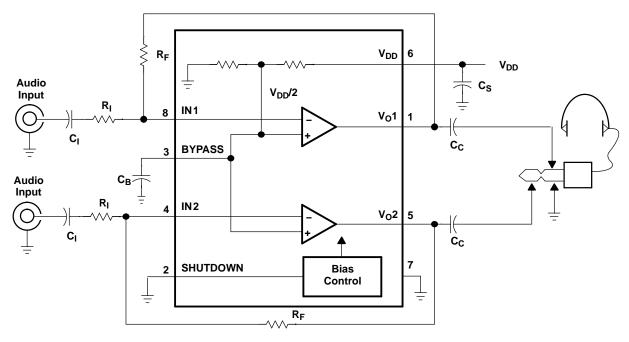
#### (TOP VIEW) $V_01$ IN1 8 SHUTDOWN 2 7 ] GND BYPASS [ 3 6 V<sub>O</sub>2 IN2 4 5

**D PACKAGE** 

## DESCRIPTION

The TPA302 is a stereo audio power amplifier capable of delivering 250 mW of continuous average power into an 8- $\Omega$  load at less than 0.06% THD+N from a 5-V power supply or up to 300 mW at 1% THD+N. The TPA302 has high current outputs for driving small unpowered speakers at 8  $\Omega$  or headphones at 32  $\Omega$ . For headphone applications driving 32- $\Omega$  loads, the TPA302 delivers 60 mW of continuous average power at less than 0.06% THD+N. The amplifier features a shutdown function for power-sensitive applications as well as internal thermal and short-circuit protection. The amplifier is available in an 8-pin SOIC (D) package that reduces board space and facilitates automated assembly.

## **TYPICAL APPLICATION CIRCUIT**



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

A





This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### **AVAILABLE OPTIONS**

	PACKAGED DEVICES
T <sub>A</sub>	SMALL OUTLINE <sup>(1)</sup> (D)
-40°C to 85°C	TPA302D

(1) The D packages are available taped and reeled. To order a taped and reeled part, add the suffix R (e.g., TPA302DR)

### **ABSOLUTE MAXIMUM RATINGS**

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		UNIT
V <sub>DD</sub>	Supply voltage	6 V
VI	Input voltage	–0.3 V to V <sub>DD</sub> + 0.3 V
	Continuous total power dissipation	Internally limited (see Dissipation Rating Table)
TJ	Operating junction temperature range	–40°C to 150° C
T <sub>stg</sub>	Storage temperature range	–65°C to 150°C
	Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

### **DISSIPATION RATING TABLE**

PACKAGE	$T_A \le 25^{\circ}C$	DERATING FACTOR	T <sub>A</sub> = 70°C	T <sub>A</sub> = 85°C	
	POWER RATING	ABOVE T <sub>A</sub> = 25°C	POWER RATING	POWER RATING	
D	731 mW	5.8 mW/°C	460 mW	380 mW	

## **RECOMMENDED OPERATING CONDITIONS**

		MIN	MAX	UNIT
V <sub>DD</sub>	Supply voltage	2.7	5.5	V
T <sub>A</sub>	Operating free-air temperature	-40	85	°C

## DC ELECTRICAL CHARACTERISTICS

at specified free-air temperature, V<sub>DD</sub> = 3.3 V (unless otherwise noted)

	PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT
I <sub>DD</sub>	Supply current			2.25	5	mA
V <sub>IO</sub>	Input offset voltage			5	20	mV
PSRR	Power supply rejection ratio	V <sub>DD</sub> = 3.2 V to 3.4 V		55		dB
I <sub>DD(SD)</sub>	Quiescent current in shutdown			0.6	20	μA

## **AC OPERATING CHARACTERISTICS**

 $V_{\text{DD}}$  = 3.3 V,  $T_{\text{A}}$  = 25°C,  $R_{\text{L}}$  = 8  $\Omega$  (unless otherwise noted)

	PARAMETER		TEST CONDITION	MIN TYP M	
			THD < 0.08%	100	
D.		Gain = -1,	THD < 1%	125	mW
Po	Output power	f = 1 kHz	THD < 0.08%, $R_{L} = 32 \Omega$	25	mvv
			THD < 1%, $R_L = 32 \Omega$	35	
B <sub>OM</sub>	Maximum output power bandwidth	Gain = 10,	1% THD	20	kHz
B <sub>1</sub>	Unity gain bandwidth	Open loop		1.5	MHz
	Channel separation	f = 1 kHz		75	dB
	Supply ripple rejection ratio	f = 1 kHz		45	dB
Vn	Noise output voltage	Gain = -1		10	μVrms

## DC ELECTRICAL CHARACTERISTICS

at specified free-air temperature,  $V_{DD} = 5$  V (unless otherwise noted)

	PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT
I <sub>DD</sub>	Supply current			4	10	mA
Voo	Output offset voltage			5	20	mV
PSRR	Power supply rejection ratio	$V_{DD} = 4.9 V \text{ to } 5.1 V$		65		dB
I <sub>DD(SD)</sub>	Quiescent current in shutdown			0.6		μΑ

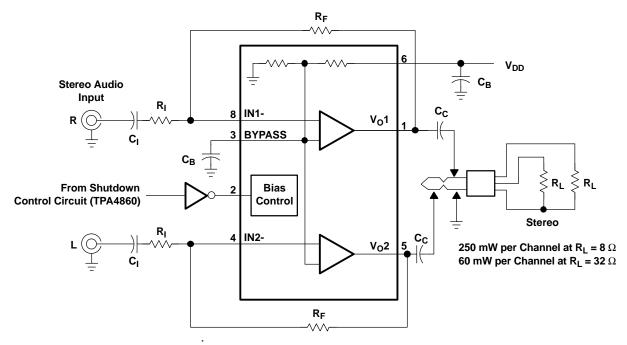
## **AC OPERATING CHARACTERISTICS**

 $V_{\text{DD}}$  = 5 V,  $T_{\text{A}}$  = 25°C,  $R_{\text{L}}$  = 8  $\Omega$  (unless otherwise noted)

	PARAMETER	٢	TEST CONDITION	MIN TYP MAX	UNIT
			THD < 0.06%	250	
Po		Gain = −1,	THD < 1%	300	mW
		f = 1 kHz	THD < 0.06%, $R_{L} = 32 \Omega$	60	mvv
			THD < 1%, $R_L = 32 \Omega$	80	
B <sub>OM</sub>	Maximum output power bandwidth	Gain = 10,	1% THD	20	kHz
B <sub>1</sub>	Unity gain bandwidth	Open loop		1.5	MHz
	Channel separation	f = 1 kHz		75	dB
	Supply ripple rejection ratio	f = 1 kHz		45	dB
V <sub>n</sub>	Noise output voltage	Gain = -1		10	μVrms



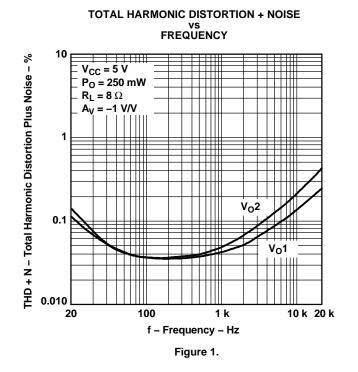
## TYPICAL APPLICATION



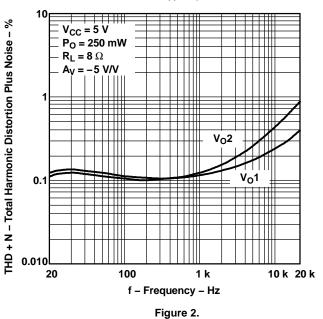
## **TYPICAL CHARACTERISTICS**

### Table of Graphs

			FIGURE
THD+N	Total harmonic distortion plus noise	vs Frequency	1-3, 7-9, 13-15, 19-21
	Total harmonic distortion plus hoise	vs Output power	4-6, 10-12 16-18, 22-24
	Supply surrent	vs Supply voltage	25
DD	Supply current	vs Free-air temperature	26
V <sub>n</sub>	Output noise voltage	vs Frequency	27, 28
	Maximum package power dissipation vs Free-air temperature		29
	Power dissipation	vs Output power	30, 31
P <sub>Omax</sub>	Maximum output power	vs Free-air temperature	32, 33
<b>D</b>		vs Load resistance	34
Po	Output power	vs Supply voltage	35
	Open-loop response		36
	Closed-loop response		37
	Crosstalk	vs Frequency	38, 39
	Supply ripple rejection ratio	vs Frequency	40, 41

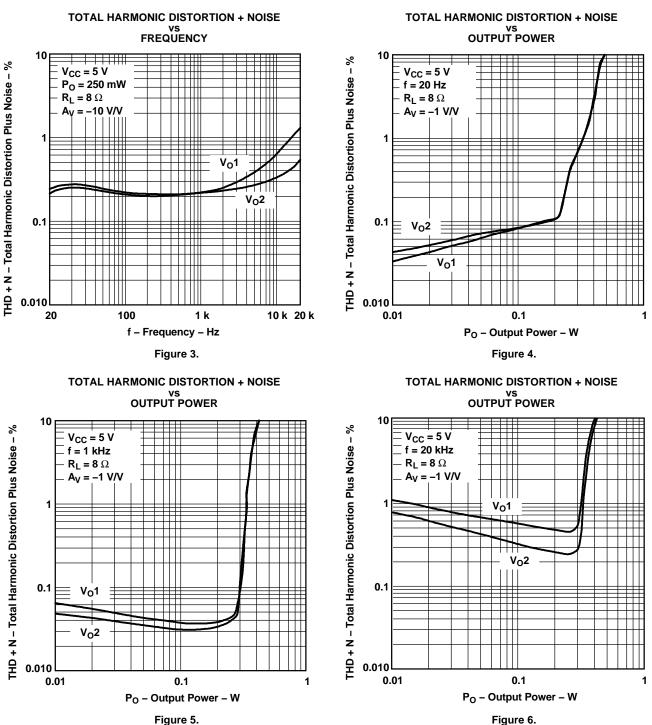


#### TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY

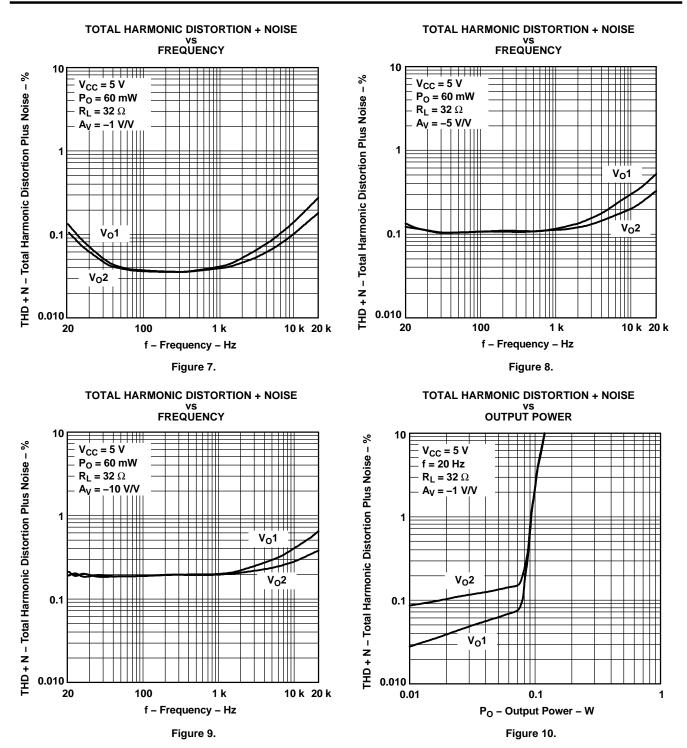










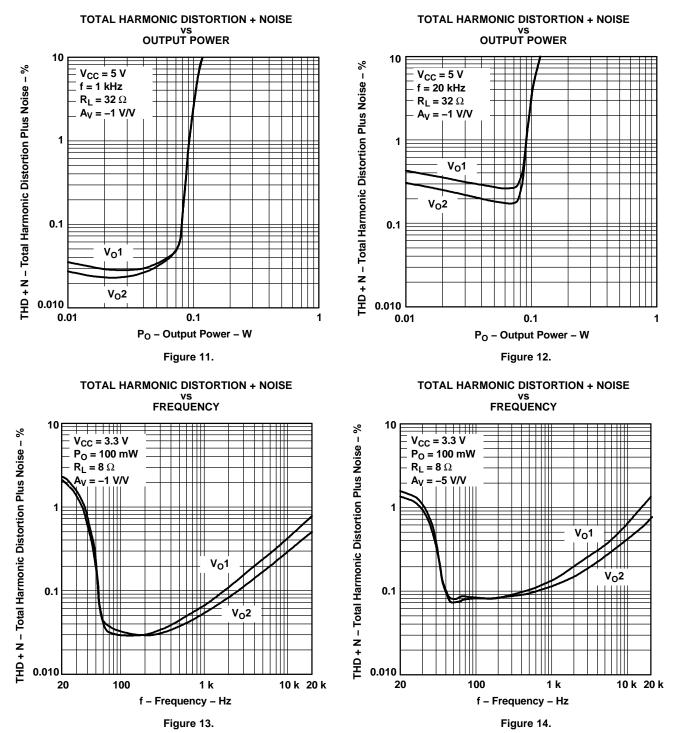


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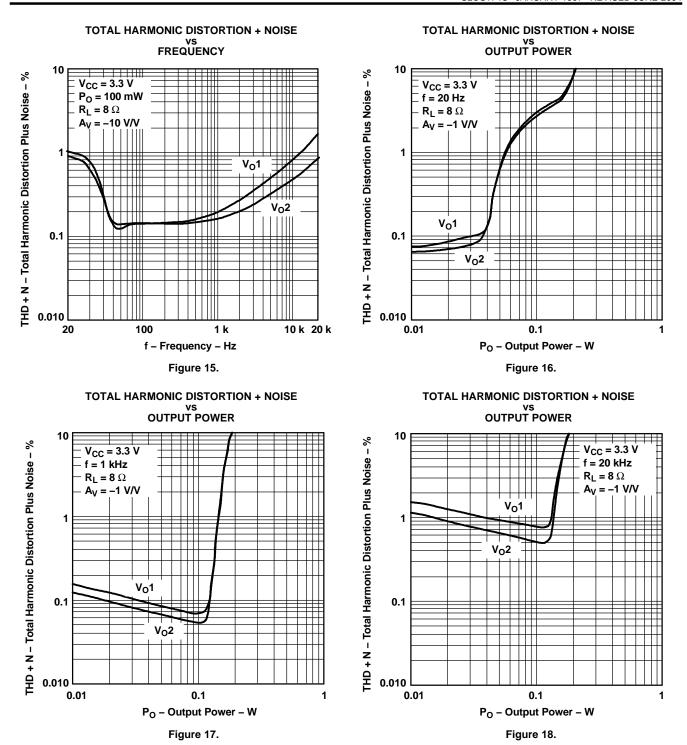
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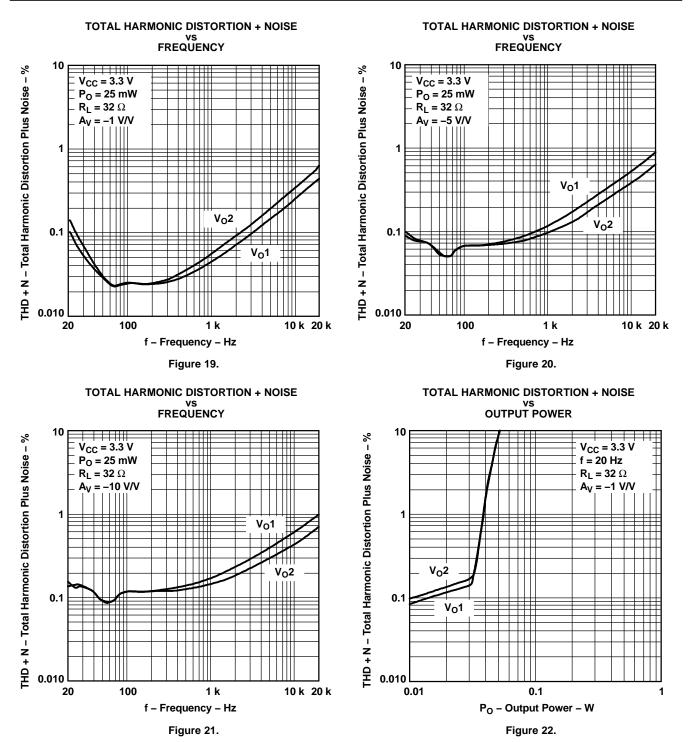


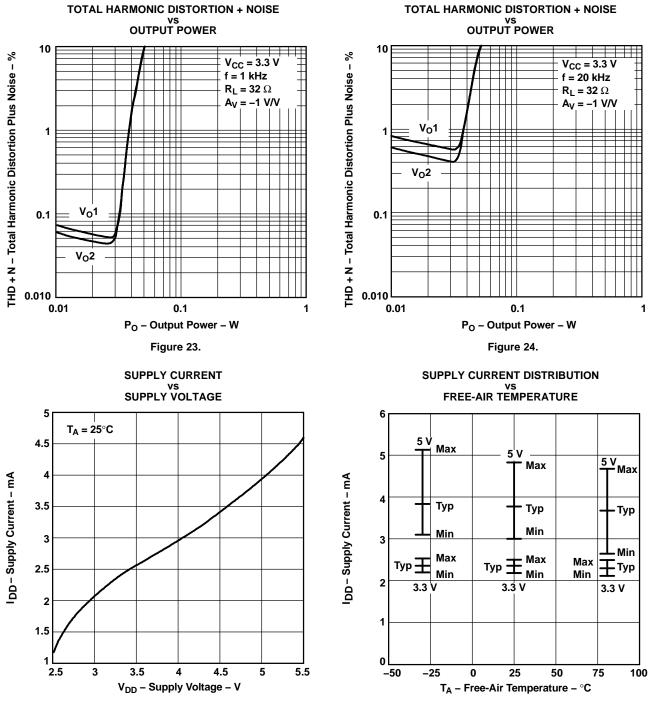
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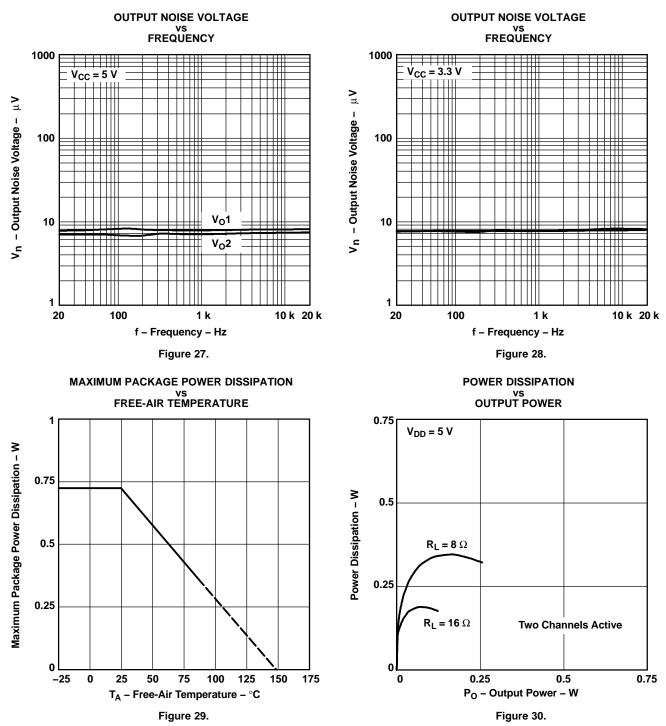


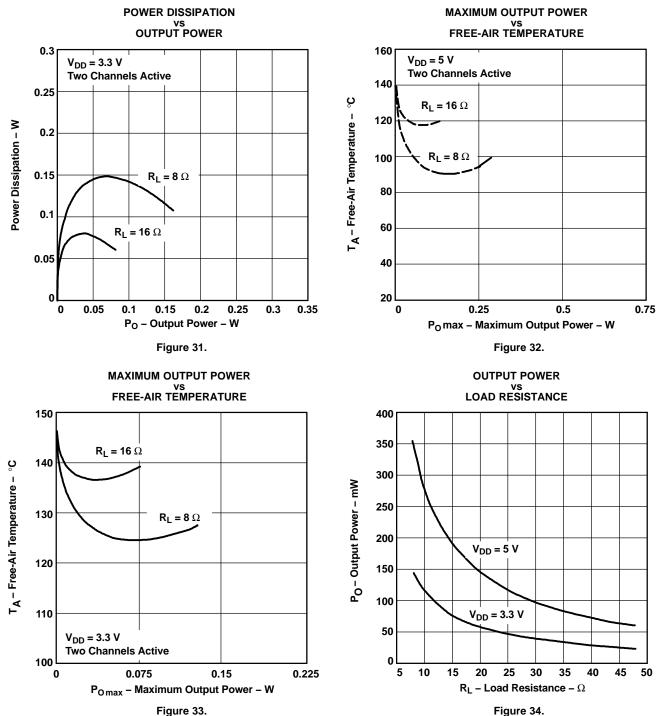
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Figure 26.

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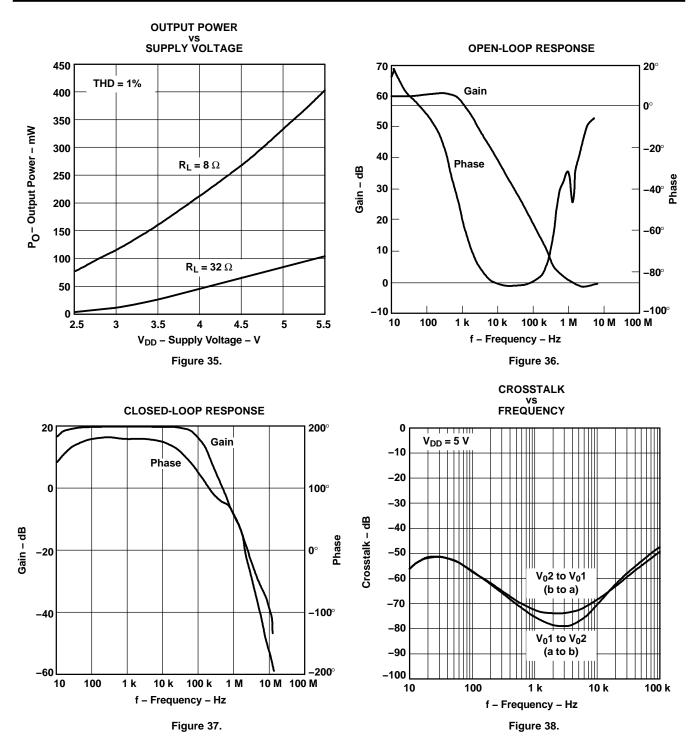




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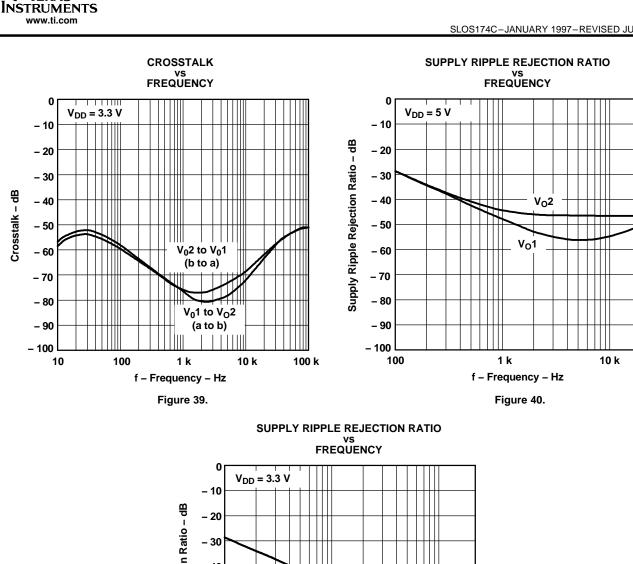
Figure 34.



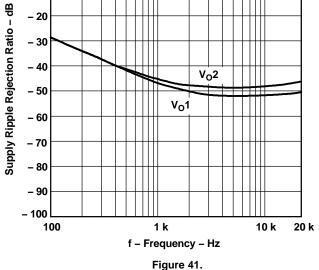


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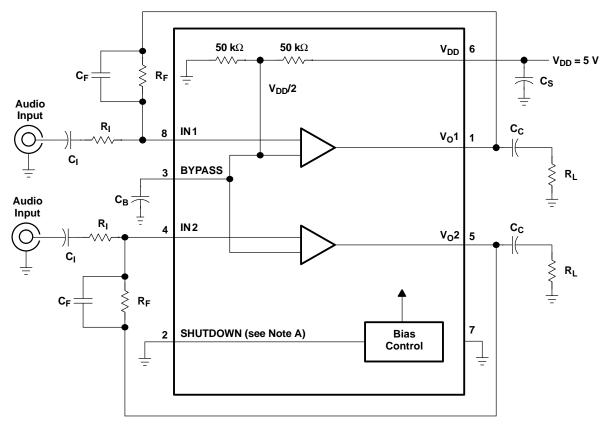
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## **APPLICATION INFORMATION**

## **SELECTION OF COMPONENTS**

Figure 42 is a schematic diagram of a typical application circuit.





#### Figure 42. TPA302 Typical Notebook Computer Application Circuit

#### Gain Setting Resistors, R<sub>F</sub> and R<sub>I</sub>

The gain for the TPA302 is set by resistors  $R_F$  and  $R_I$  according to Equation 1.

$$Gain = -\left(\frac{R_F}{R_I}\right)$$
(1)

Given that the TPA302 is an MOS amplifier, the input impedance is high; consequently, input leakage currents are not generally a concern, although noise in the circuit increases as the value of  $R_F$  increases. In addition, a certain range of  $R_F$  values is required for proper start-up operation of the amplifier. Taken together, it is recommended that the effective impedance seen by the inverting node of the amplifier be set between 5 k $\Omega$  and 20 k $\Omega$ . The effective impedance is calculated in Equation 2.

Effective Impedance = 
$$\frac{R_F R_I}{R_F + R_I}$$

(2)

As an example, consider an input resistance of 10 k $\Omega$  and a feedback resistor of 50 k $\Omega$ . The gain of the amplifier would be -5 and the effective impedance at the inverting terminal would be 8.3 k $\Omega$ , which is within the recommended range.

(3)

### **APPLICATION INFORMATION (continued)**

For high-performance applications, metal film resistors are recommended because they tend to have lower noise levels than carbon resistors. For values of  $R_F$  above 50 k $\Omega$ , the amplifier tends to become unstable due to a pole formed from  $R_F$  and the inherent input capacitance of the MOS input structure. For this reason, a small compensation capacitor of approximately 5 pF should be placed in parallel with  $R_F$ . In effect, this creates a low-pass filter network with the cutoff frequency defined in Equation 3.

$$f_{c(lowpass)} = \frac{1}{2\pi R_F C_F}$$

For example, if  $R_F$  is 100 k $\Omega$  and  $C_F$  is 5 pF, then  $f_{c(lowpass)}$  is 318 kHz, which is well outside of the audio range.

#### Input Capacitor, C<sub>1</sub>

In the typical application, input capacitor  $C_1$  is required to allow the amplifier to bias the input signal to the proper dc level for optimum operation. In this case,  $C_1$  and  $R_1$  form a high-pass filter with the corner frequency determined in Equation 4.

$$f_{c(highpass)} = \frac{1}{2\pi R_{|}C_{|}}$$
(4)

The value of C<sub>1</sub> is important to consider as it directly affects the bass (low-frequency) performance of the circuit. Consider the example where R<sub>1</sub> is 10 k $\Omega$  and the specification calls for a flat bass response down to 40 Hz. Equation 4 is reconfigured as Equation 5.

$$C_{l} = \frac{1}{2\pi R_{l} f_{c}(highpass)}$$
(5)

In this example,  $C_I$  is 0.4  $\mu$ F; so, one would likely choose a value in the range of 0.47  $\mu$ F to 1  $\mu$ F. A further consideration for this capacitor is the leakage path from the input source through the input network ( $R_I$ ,  $C_I$ ) and the feedback resistor ( $R_F$ ) to the load. This leakage current creates a dc offset voltage at the input to the amplifier that reduces useful headroom, especially in high-gain applications (>10). For this reason, a low-leakage tantalum or ceramic capacitor is the best choice. When polarized capacitors are used, the positive side of the capacitor should face the amplifier input in most applications as the dc level there is held at  $V_{DD}/2$ , which is likely higher than the source dc level. Note that it is important to confirm the capacitor polarity in the application.

#### Power Supply Decoupling, C<sub>S</sub>

The TPA302 is a high-performance CMOS audio amplifier that requires adequate power supply decoupling to ensure that the output total harmonic distortion (THD) is as low as possible. Power supply decoupling also prevents oscillations for long lead lengths between the amplifier and the speaker. The optimum decoupling is achieved by using two capacitors of different types that target different types of noise on the power supply leads. For higher frequency transients, spikes, or digital hash on the line, a good low equivalent-series-resistance (ESR) ceramic capacitor, typically 0.1  $\mu$ F, placed as close as possible to the device V<sub>DD</sub> lead, works best. For filtering lower frequency noise signals, a larger aluminum electrolytic capacitor of 10  $\mu$ F or greater placed near the power amplifier is recommended.

#### Midrail Bypass Capacitor, C<sub>B</sub>

The midrail bypass capacitor,  $C_B$ , serves several important functions. During startup or recovery from shutdown mode,  $C_B$  determines the rate at which the amplifier starts up. This helps to push the start-up pop noise into the subaudible range (so low it cannot be heard). The second function is to reduce noise produced by the power supply caused by coupling into the output drive signal. This noise is from the midrail generation circuit internal to the amplifier. The capacitor is fed from a 25-k $\Omega$  source inside the amplifier. To keep the start-up pop as low as possible, the relationship shown in Equation 6 should be maintained.

$$\frac{1}{\left(\mathsf{C}_{\mathsf{B}} \times 25 \,\mathsf{k}\Omega\right)} \leq \frac{1}{\left(\mathsf{C}_{\mathsf{I}}\mathsf{R}_{\mathsf{I}}\right)} \tag{6}$$

As an example, consider a circuit where C<sub>B</sub> is 0.1  $\mu$ F, C<sub>I</sub> is 0.22  $\mu$ F and R<sub>I</sub> is 10 k $\Omega$ . Inserting these values into Equation 6 results in: 400  $\leq$  454 which satisfies the rule. Recommended values for bypass capacitor C<sub>B</sub> are 0.1- $\mu$ F to 1- $\mu$ F, ceramic or tantalum low-ESR, for the best THD and noise performance.



### **APPLICATION INFORMATION (continued)**

### **OUTPUT COUPLING CAPACITOR, Cc**

In the typical single-supply, single-ended (SE) configuration, an output coupling capacitor ( $C_C$ ) is required to block the dc bias at the output of the amplifier thus preventing dc currents in the load. As with the input coupling capacitor, the output coupling capacitor and impedance of the load form a high-pass filter governed by Equation 7.

$$f_{C} = \frac{1}{2\pi R_{I} C_{C}}$$

(7)

The main disadvantage, from a performance standpoint, is that the load impedances are typically small, which drives the low-frequency corner higher. Large values of  $C_C$  are required to pass low frequencies into the load. Consider the example where a  $C_C$  of 68 µF is chosen and loads vary from 8  $\Omega$ , 32  $\Omega$ , and 47 k $\Omega$ . Table 1 summarizes the frequency response characteristics of each configuration.

# Table 1. Common Load Impedances vs Low Frequency Output Characteristics in SE Mode

RL	C <sub>C</sub>	LOWEST FREQUENCY
8 Ω	68 µF	293 Hz
32 Ω	68 µF	73 Hz
47,000 Ω	68 µF	0.05 Hz

As Table 1 indicates, most of the bass response is attenuated into 8- $\Omega$  loads while headphone response is adequate and drive into line level inputs (a home stereo for example) is good.

The output coupling capacitor required in single-supply, SE mode also places additional constraints on the selection of other components in the amplifier circuit. The rules described previously still hold with the addition of the following relationship:

$$\frac{1}{\left(\mathsf{C}_{\mathsf{B}}\times 25\,\mathsf{k}\Omega\right)} \leq \frac{1}{\left(\mathsf{C}_{\mathsf{I}}\mathsf{R}_{\mathsf{I}}\right)} \ll \frac{1}{\mathsf{R}_{\mathsf{L}}\mathsf{C}_{\mathsf{C}}}$$

(8)

## SHUTDOWN MODE

The TPA302 employs a shutdown mode of operation designed to reduce quiescent supply current,  $I_{DD(q)}$ , to the absolute minimum level during periods of nonuse for battery-power conservation. For example, during device sleep modes or when other audio-drive currents are used (i.e., headphone mode), the speaker drive is not required. The SHUTDOWN input terminal should be held low during normal operation when the amplifier is in use. Pulling SHUTDOWN high causes the outputs to mute and the amplifier to enter a low-current state,  $I_{DD} \sim 0.6 \ \mu$ A. SHUTDOWN should never be left unconnected because amplifier operation would be unpredictable.

## USING LOW-ESR CAPACITORS

Low-ESR capacitors are recommended throughout this applications section. A real capacitor can be modeled simply as a resistor in series with an ideal capacitor. The voltage drop across this resistor minimizes the beneficial effects of the capacitor in the circuit. The lower the equivalent value of this resistance the more the real capacitor behaves like an ideal capacitor.

## THERMAL CONSIDERATIONS

A prime consideration when designing an audio amplifier circuit is internal power dissipation in the device. The curve in Figure 43 provides an easy way to determine what output power can be expected out of the TPA302 for a given system ambient temperature in designs using 5-V supplies. This curve assumes no forced airflow or additional heat sinking.

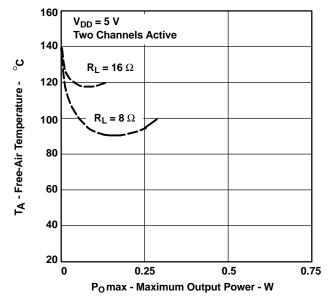


Figure 43. Free-Air Temperature Versus Maximum Output Power

## **5-V VERSUS 3.3-V OPERATION**

The TPA302 was designed for operation over a supply range of 2.7 V to 5.5 V. This data sheet provides full specifications for 5-V and 3.3-V operation because they are considered to be the two most common standard voltages. There are no special considerations for 3.3-V versus 5-V operation as far as supply bypassing, gain setting, or stability. Supply current is slightly reduced from 4 mA (typical) to 2.25 mA (typical). The most important consideration is that of output power. Each amplifier in the TPA302 can produce a maximum voltage swing of  $V_{DD} - 1$  V. This means, for 3.3-V operation, clipping starts to occur when  $V_{O(PP)} = 2.3$  V as opposed when  $V_{O(PP)} = 4$  V while operating at 5 V. The reduced voltage swing subsequently reduces maximum output power into the load before distortion begins to become significant.



10-Dec-2020

## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPA302D	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		TPA302	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(<sup>6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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## TUBE



#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
TPA302D	D	SOIC	8	75	505.46	6.76	3810	4

## **D0008A**



## **PACKAGE OUTLINE**

## SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.

- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- This dimension does not include interlead flash.
   Reference JEDEC registration MS-012, variation AA.



## D0008A

## **EXAMPLE BOARD LAYOUT**

## SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



## D0008A

## **EXAMPLE STENCIL DESIGN**

## SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



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